



Sheet 1 of 7

FORM PTO-1449
(REV. 6-89)

U.S. DEPARTMENT OF COMMERCE
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Attorney's Docket No.
22920-06460

Serial No.
10/087,408

INFORMATION DISCLOSURE CITATION

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Applicant:
Xiaodong Huang et al.

Filing Date
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U.S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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<i>JD</i>	3	5,614,435	3/25/97	Petroff et al.	437	110	10/27/94

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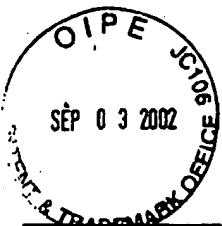


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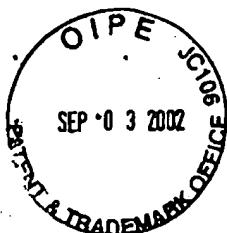
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FORM PTO-1449 (REV. 6-89)		U.S. DEPARTMENT OF COMMERCE Patent and Trademark Office		Attorney's Docket No. 22920-06460	Serial No. 10/087,408
INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)		Applicant Xiaodong Huang et al.			
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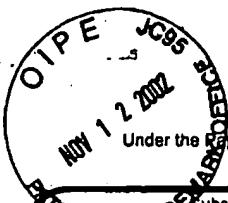
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EXAMINER <i>James Davis</i>		DATE CONSIDERED <i>2/01/04</i>		
<p>EXAMINER: Initial if references considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered.</p> <p>Include copy of this form with next communication to applicant.</p>				



Sheet 7 of 7

FORM PTO-1449 (REV. 6-89)		U.S. DEPARTMENT OF COMMERCE Patent and Trademark Office	Attorney's Docket No. 22920-06460	Serial No. 10/087,408
INFORMATION DISCLOSURE CITATION <small>(Use several sheets if necessary)</small>		Applicant	Xiaodong Huang et al.	
		Filing Date March 1, 2002	Group Art Unit Unassigned	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)				
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EXAMINER <u>James Davis</u> DATE CONSIDERED <u>2/07/04</u>				
EXAMINER: Initial if references considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.				

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REV: 02/01



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INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

Sheet

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of

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Complete if Known

Application No.	10/087,408
Filing Date	March 1, 2002
First Named Inventor	Xiaodong Huang
Art Unit	2881
Examiner Name	Not yet known

Attorney Docket Number

22920-06460

U.S. PATENT DOCUMENTS

		Document No.			
Examiner Initials*	Cite No. ¹	Number – Kind Code ² (if known)	Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	
	A	US-5,541,949	07/30/1998	Bhat et al.	
	B	US-5,543,354	08/06/1998	Richard et al.	
	C	US-5,557,827	09/17/1998	Schneider, Jr. et al.	
	D	US-5,710,436	01/20/1998	Tanamoto et al.	
	E	US-5,714,765	02/03/1998	Noetzel et al.	
	F	US-5,881,086	03/09/1999	Miyazawa	
	G	US-5,953,356	09/14/1999	Botez et al.	
	H	US-6,117,699	09/12/2000	Lemoff et al.	
	I	US-6,177,684	01/23/2001	Sugiyama	
	J	US-6,285,704	09/04/2001	Kullander-Sjoberg et al.	
	K	US-6,329,668	12/11/2001	Razeghi	

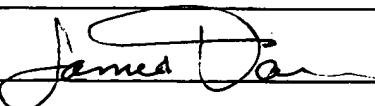
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		Foreign Patent Document			
Examiner Initials*	Cite No. ¹	Country Code ³ – Number ⁴ Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	T ⁶

OTHER REFERENCES – NON-PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ⁶
JD	L	U.S. Patent Application Publication, US 2001/0050934, December 13, 2001; Choquette et al.	

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Examiner Signature		Date Considered	2/03/04
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<i>Complete if Known</i>	
Application N.	10/087,408
Filing Date	March 1, 2002
First Named Inventor	Xiaodong Huang
Art Unit	2828
Examiner Name	James W. Davie
Attorney Docket Number	22920-06460

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Examiner Initials*	Cite No. ¹	Document No.	Number – Kind Code ² (if known)	Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
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<i>JW</i>	2	US-5,930,278 A	07-27-1999	Menigaux	

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Examiner Signature	<i>James W. Davie</i>	Date Considered	<i>2/3/04</i>
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Examiner Name	James W. Davie	
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JD	8	Park, Gyoungwon et al., "Temperature Dependence of Gain Saturation in Multilevel Quantum Dot Lasers," <i>IEEE Journal of Quantum Electronics</i> , IEEE Inc., New York, U.S., Vol. 36, No. 9, September 2000, pages 1065-1071.	
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First Named Inventor	Xiaodong Huang		
Art Unit	2828		
Examiner Name	James W. Davie		
Attorney Docket Number	22920-06460		

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DS	1	US-5,608,229 A		03-04-1997	Mukai et al.

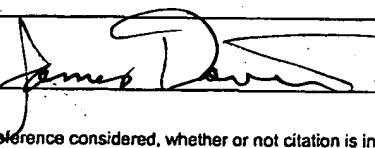
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DS	2	Komori, Kazuhiro et al., "Noise Study of Low-Dimensional Quantum-Well Semiconductor Laser Amplifiers," <i>IEEE Journal of Quantum Electronics</i> , IEEE Inc., New York, US, Vol. 28, No. 9, September 1, 1992, pages 1894-1900.	
DS	3	Saito, Hideaki et al., "Room-temperature lasing operation of a Quantum-dot vertical-cavity surface-emitting laser," <i>Applied Physics Letters</i> , American Institute of Physics, New York, US, Vol. 69, No. 21, November 18, 1996, pages 3140-3142.	
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